

GSDSS22W Series

Surface Mount Schottky Rectifiers

Product Description

Reverse Voltage 20V to 100V Forward Current 2.0A

Features

- Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity diodes in surface mount applications
- Schottky barrier junction, majority carrier conduction
- Guard ring for stress protection
- Low forward voltage drop
- High current capability
- High surge capability
- High reliability
- Lead(Pb)-Free

Mechanical Data

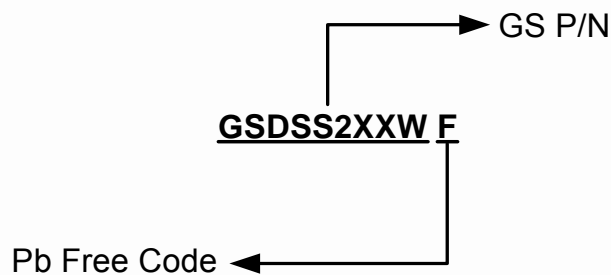
- Case : Molded plastic, SMA(W) Package
- Epoxy meets flammability requirements per UL 94V-0
- All terminal leads are readily solderable
- Weight approx : 70 mg

Packages



SMA(W)
Color Band Denotes CATHODE

Ordering Information



Part Number	Package	Quantity
GSDSS22WF Series	SMA(W)	5000 PCS

Marking Information

P/N	Part Marking	Package
GSDSS22WF	S22W	SMA(W)
GSDSS23WF	S23W	SMA(W)
GSDSS24WF	S24W	SMA(W)
GSDSS25WF	S25W	SMA(W)
GSDSS26WF	S26W	SMA(W)
GSDSS28WF	S28W	SMA(W)
GSDSS210WF	S2AW	SMA(W)

Electrical Characteristics

(Rating 25°C Ambient Temperature Unless Otherwise Specified.)

Symbol	Conditions	GSDSS22WF	GSDSS23WF	GSDSS24WF	GSDSS25WF	Unit
V_{RRM}	Maximum Recurrent Peak Reverse Voltage	20	30	40	50	V
V_{RMS}	Maximum RMS Voltage	14	21	28	35	V
V_{DC}	Maximum DC Blocking Voltage	20	30	40	50	V
V_F	Maximum Instantaneous At 2.0A DC	0.45	0.55		0.70	V
Symbol	Conditions	GSDSS26WF	GSDSS28WF	GSDSS210WF		Unit
V_{RRM}	Maximum Recurrent Peak Reverse Voltage	60	80	100		V
V_{RMS}	Maximum RMS Voltage	42	56	70		V
V_{DC}	Maximum DC Blocking Voltage	60	80	100		V
V_F	Maximum Instantaneous At 2.0A DC	0.70	0.85			V
I_R	Maximum Reverse Leakage Current at rated V_R	$T_J = 25^\circ\text{C}$	0.5			mA
		$T_J = 125^\circ\text{C}$	20			
$I_{F(AV)}$	Maximum Average Forward Rectified Current	2.0				A
I_{FSM}	Peak Forward Surge Current (8.3ms Single Half Sine-Wave)	50				A
$R_{\theta JL}$	Typical Thermal Resistance (Junction to lead)	35				$^\circ\text{C/W}$
T_J	Operating Temperature Range	-55 to +125				$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to +150				$^\circ\text{C}$

Typical Characteristics

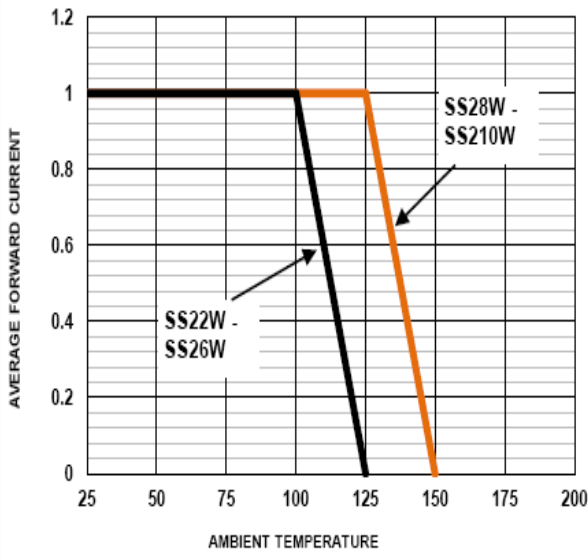


Figure 1. Forward Current Derating Curve

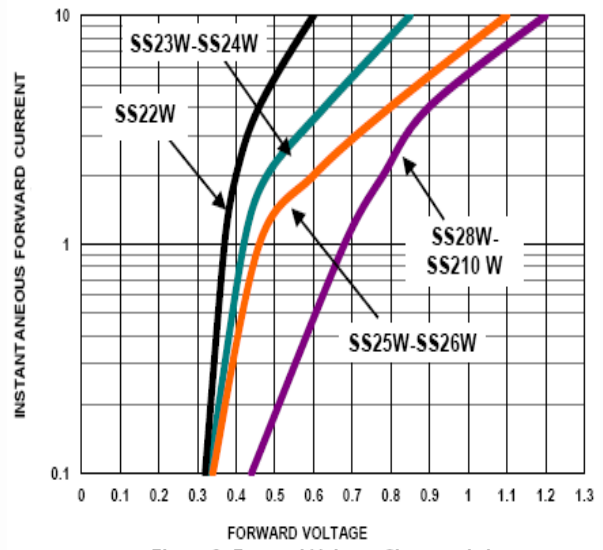


Figure 2. Forward Voltage Characteristics

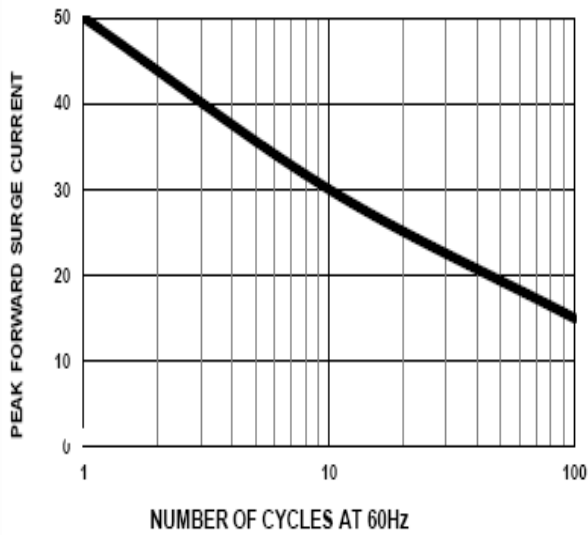


Figure 3. Non-Repetitive Surge Current

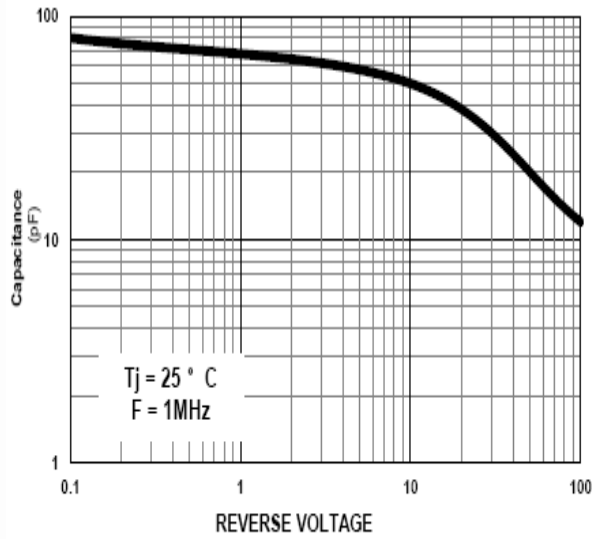
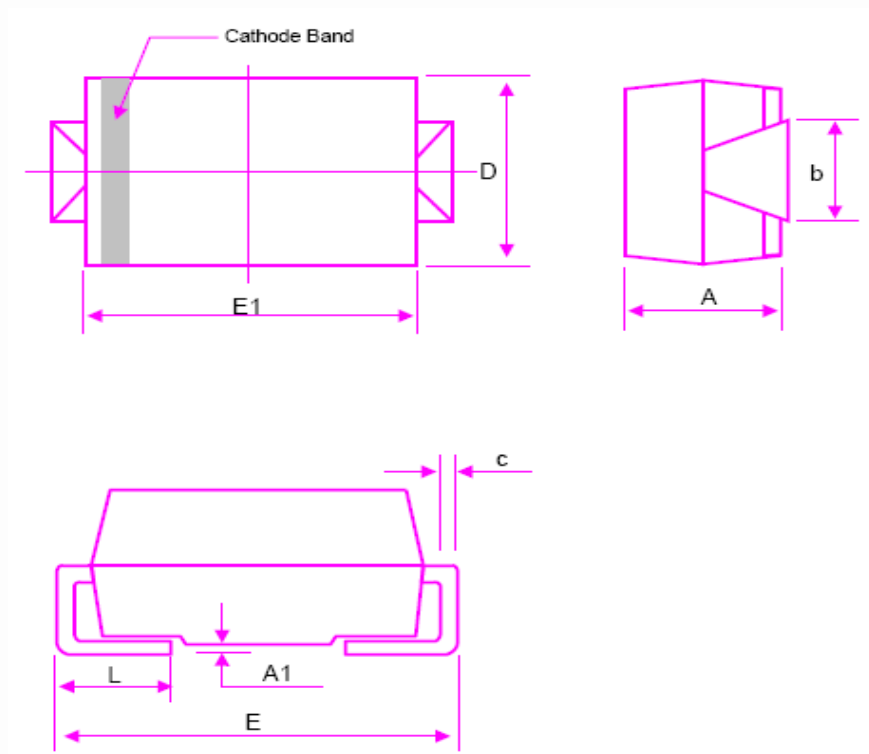


Figure 4. Junction Capacitance

Package Dimension

SMA(W)



Dimensions

Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	1.70	2.31	0.067	0.091
A1	0.10	0.20	0.004	0.008
b	1.29	1.70	0.051	0.067
c	0.15	0.31	0.006	0.012
D	2.18	2.79	0.086	0.110
E	4.70	5.31	0.185	0.209
E1	4.06	4.57	0.160	0.180
L	0.89	1.50	0.035	0.059

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